

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	34	((band adj type) or (band-type)) near electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:17
S2	23	((band adj type) or (band-type)) near conduct\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:18
S3	6	((band adj type) or (band-type)) near conductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:38
S4	6	((band adj type) or (band-type)) near conductive	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:29
S5	4687	((band adj type) or (band-type))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:38
S6	123	S5 and wafer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:38
S7	666304	conductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:38
S8	73739	bit-line or (bit adj line)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:38
S9	9239	S7 and S8	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:38
S10	0	S6 and S9	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:39

S11	1	S9 and S5	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:45
S12	7271	storage adj electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:46
S13	978	secondary adj mold	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:46
S14	0	S12 and S13	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:46
S15	213433	tungsten	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:46
S16	134565	silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:46
S17	112510	polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:48
S18	125092	silicon adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:48
S19	25720	TEOS	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:48
S20	613	PTEOS	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:49

S21	285637	insulator	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:49
S22	666304	conductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:49
S23	10454	ArF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:49
S24	11899	KrF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:49
S25	6813	S23 and S24	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:49
S26	675	S25 and S22	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:50
S27	256	S26 and S21	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:50
S28	398545	line and band	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:51
S29	92	S27 and S28	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:51
S30	4	S29 and S19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:56

S31	196	diagonal near electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:57
S32	0	(zg adj zag) near electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 10:57
S33	51	S31 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:23
S34	1	10/731931	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 07:57
S35	1	09/426108	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:23
S36	7	"6344379"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:26
S37	1486212	electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:26
S38	399468	branch	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:26
S39	0	S37 adj S36	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:26
S40	395	S37 adj S38	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:31

S41	688	S37 near S38	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:26
S42	520637	space near between	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:31
S43	3124856	increase	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:31
S44	3074	S43 near "44"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:31
S45	1486212	electrodes	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:31
S46	439	S44 and S45	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:32
S47	7	S44 near S45	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:33
S48	779437	array	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:33
S49	12782	S45 near S48	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:33
S50	3111	S49 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:34

S51	139189	diagonal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:34
S52	229	S51 and S50	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:42
S53	107441	DRAM	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:55
S54	1486212	electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:42
S55	1603104	pattern	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:42
S56	27135	S54 near S55	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:43
S57	847	S56 and S53	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:44
S58	139189	diagonal	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:44
S59	20	S57 and S58	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:44
S60	702	S53 and S25	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:55

S61	118	S60 and S16	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:56
S62	66	S61 and S17	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 12:30
S63	57	S62 and S18	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:56
S64	19	S63 and S19	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 12:06
S65	0	S64 and S20	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:56
S66	5	S64 and S21	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:57
S67	2	S64 and S22	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 11:57
S68	3	09/904591	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 12:30
S69	2	09/903580	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/02 12:30
S70	2	"6403413".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 07:57

S71	134829	silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 14:12
S72	112701	polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 14:12
S73	125324	silicon adj oxide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 14:12
S74	10479	ArF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 14:12
S75	11926	KrF	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 14:12
S76	6830	S74 and S75	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 14:12
S77	107631	DRAM	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 14:12
S78	702	S77 and S76	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 14:12
S79	118	S78 and S71	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 14:12
S80	66	S79 and S72	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 14:12

S81	57	S80 and S73	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 14:16
S82	5186	polysilicon near electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 14:17
S83	1437981	wide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 14:17
S84	1699340	width	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 14:17
S85	336	"113" near (S83 or S84)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 14:24
S86	1487064	electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 14:25
S87	4275	extentions	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 14:25
S88	5	S86 near S87	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 14:29
S89	3475814	contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 14:29
S90	1547367	semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 14:29

S91	392333	S89 and S90	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 14:30
S92	3896	S91 and (storage adj electrode)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 14:31
S93	122623	S92 ana DRAM	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 14:31
S94	2186	S92 and DRAM	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 14:31
S95	1589	S94 and polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 14:31
S96	1589	S95 and contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 14:32
S97	788	S96 and shape	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 14:32
S98	184	S97 and stack	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 14:59
S99	2	"6381165".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 15:01
S100	2	"6885052".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 15:04

S10 1	2	"6492701".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 15:09
S10 2	1	10/731931	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 15:10
S10 3	0	("2004/0127050").URPN.	USPAT	OR	ON	2005/08/04 15:10
S10 4	554204	electrode nead mold	USPAT	OR	ON	2005/08/04 15:10
S10 5	215016	mold	USPAT	OR	ON	2005/08/04 15:11
S10 6	2795	storage adj electrode	USPAT	OR	ON	2005/08/04 15:11
S10 7	2	S106 near S105	USPAT	OR	ON	2005/08/04 15:12
S10 8	76014	etch	USPAT	OR	ON	2005/08/04 15:12
S10 9	855328	etch or remove	USPAT	OR	ON	2005/08/04 15:13
S11 0	2817964	form	USPAT	OR	ON	2005/08/04 15:13
S11 1	4115	S109 near S110	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 15:13
S11 2	1	S111 near S106	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 15:14
S11 3	914	molded near electrode	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 15:14
S11 4	132	S113 and semiconductor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 15:19

S11 5	0	S113 and semiconducto45 and DRAM	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 15:19
S11 6	4	S114 and DRAM	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 16:04
S11 7	2	09/920927	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 16:10
S11 8	4	09/749463	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 17:50
S11 9	12036	hard adj mask	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 17:50
S12 0	134829	silicon adj nitride	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 17:50
S12 1	420	S119 near S120	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 17:51
S12 2	24	S119 near S120.ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/04 17:51